RoHS

COMPLIANT

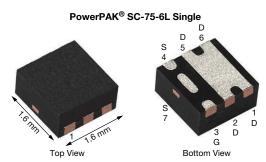
HALOGEN

FREE

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Vishay Siliconix

N-Channel 20 V (D-S) MOSFET



Marking code: AF

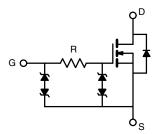
PRODUCT SUMMARY	
V _{DS} (V)	20
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.030
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 2.5 \text{ V}$	0.041
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 1.8 \text{ V}$	0.057
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 1.5 \text{ V}$	0.082
Q _g typ. (nC)	6
I _D (A) ^a	9
Configuration	Single

FEATURES

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK® SC-75 package
 - Small footprint area
 - Low on-resistance
 - Thin 0.75 mm profile
- Typical ESD protection 4000 V
- 100 % R_a tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Portable devices
 - Load switch
 - Battery switch



ORDERING INFORMATION	
Package	PowerPAK SC-75
Lead (Pb)-free and halogen-free	SiB422EDK-T1-GE3

ABSOLUTE MAXIMUM RATINGS	$(T_A = 25 ^{\circ}C, \text{ unless})$	s otherwise	noted)			
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V_{DS}	20	V		
Gate-source voltage		V_{GS}	± 8	v		
	T _C = 25 °C		9 a			
Continuous dusin surrent (T. 150 °C)	T _C = 70 °C	1 , 1	9 a			
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	l _D	7.1 ^{b, c}			
	T _A = 70 °C]	5.7 ^{b, c}	Α		
Pulsed drain current		I _{DM}	25			
Continuous source drain diede surrent	T _C = 25 °C		9 a			
Continuous source-drain diode current	T _A = 25 °C	l _S	2.1 ^{b, c}			
	T _C = 25 °C		13			
Manipular and adjusting sking	T _C = 70 °C	5	8.4	□ w		
Maximum power dissipation	T _A = 25 °C	P _D	2.5 ^{b, c}	VV		
	T _A = 70 °C		1.6 ^{b, c}			
Operating junction and storage temperature ra	inge	T _J , T _{stg}	-55 to +150	°C		
Soldering recommendations (peak temperature	e) ^{d, e}		260			

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R _{thJA}	41	51	°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	7.5	9.5	C/VV				

- a. Package limited, T_C = 25 °C b. Surface mounted on 1" x 1" FR4 board
- c. t = 5 s
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 105 °C/W

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT			
Static				•					
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V, } I_D = 250 \mu\text{A}$	20	-	-	V			
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	J 050 A	-	18	-) //0.0			
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-2.5	-	mV/°C			
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.4	-	1.0	V			
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$	-	-	± 1.5				
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	-	-	± 25	•			
Zarra maka walka na alumina awarant	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V	-	-	1	μA			
Zero gate voltage drain current		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	-	-	10				
On-state drain current a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	15	-	-	Α			
		$V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$	-	0.025	0.030				
Duning and the contract of the		$V_{GS} = 2.5 \text{ V}, I_D = 4.3 \text{ A}$	-	0.034	0.041	0			
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 1.8 V, I _D = 1.5 A	-	0.046	0.057	Ω			
		V _{GS} = 1.5 V, I _D = 1 A	-	0.055	0.082	1			
Forward transconductance a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 5 \text{ A}$	-	28	-	S			
Dynamic ^b				•					
	Qg	$V_{DS} = 10 \text{ V}, V_{GS} = 8 \text{ V}, I_D = 7.1 \text{ A}$	-	11.5	18	nC			
Total gate charge			-	6	9				
Gate-source charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 7.1 \text{ A}$	-	0.8	-				
Gate-drain charge	Q_{gd}		-	1.6	-				
Gate resistance	R_g	f = 1 MHz	460	2300	4600	Ω			
Turn-on delay time	t _{d(on)}		-	0.3	0.45				
Rise time	t _r	$V_{DD} = 10 \text{ V}, R_{L} = 1.8 \Omega$	-	0.6	0.9	μs			
Turn-off delay time	t _{d(off)}	$I_D \cong 5.7 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	3.8	6				
Fall time	t _f		-	1.7	2.6				
Turn-on delay time	t _{d(on)}		-	0.15	0.25				
Rise time	t _r	$V_{DD} = 10 \text{ V}, R_{I} = 1.8 \Omega$	-	0.3	0.45				
Turn-off delay time	t _{d(off)}	$I_D \cong 5.7 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	5.6	9				
Fall time	t _f		-	1.6	2.5				
Drain-Source Body Diode Characteristic	s								
Continuous source-drain diode current	Is	T _C = 25 °C	-	-	9				
Pulse diode forward current	I _{SM}		-	-	25	A			
Body diode voltage	V _{SD}	$I_S = 5.7 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.85	1.2	V			
Body diode reverse recovery time	t _{rr}	-	-	15	30	ns			
Body diode reverse recovery charge			-	7.5	15	nC			
Reverse recovery fall time	t _a	$T_J = 25 ^{\circ}\text{C}$	-	8	-				
Reverse recovery rise time	t _b		_	15	-	ns			

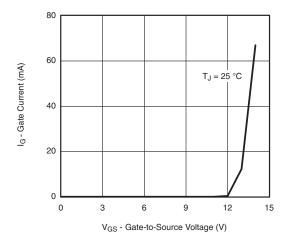
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

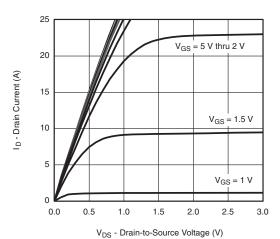
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



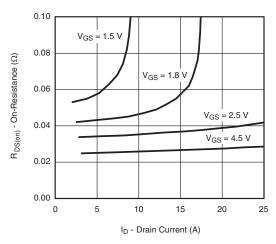
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



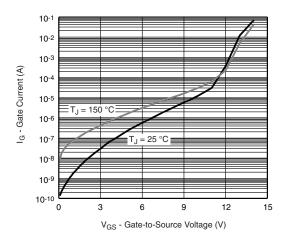
Gate Current vs. Gate-to-Source Voltage



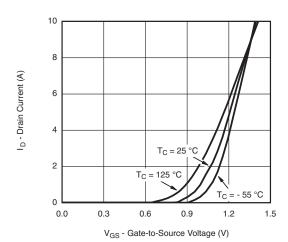
Output Characteristics



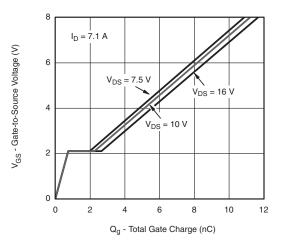
On-Resistance vs. Drain Current



Gate Current vs. Gate-to-Source Voltage



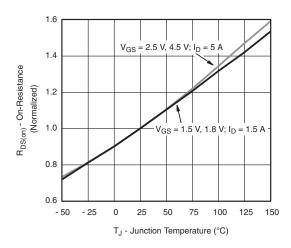
Transfer Characteristics



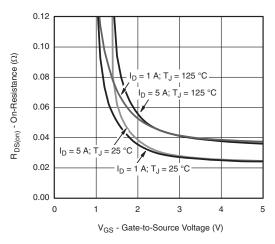
Gate Charge



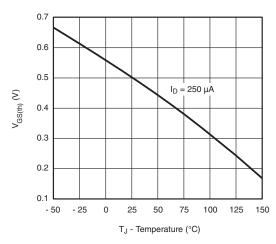
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



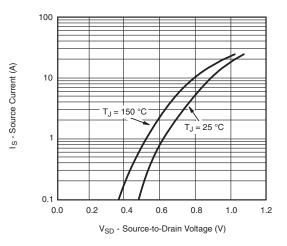
Normalized On-Resistance vs. Junction Temperature



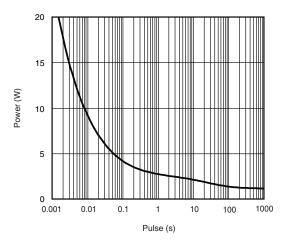
On-Resistance vs. Gate-to-Source Voltage



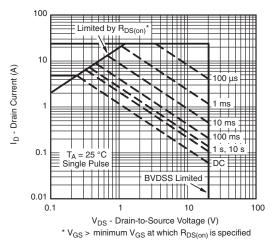
Threshold Voltage



Source-Drain Diode Forward Voltage



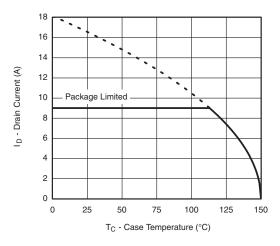
Single Pulse Power, Junction-to-Ambient

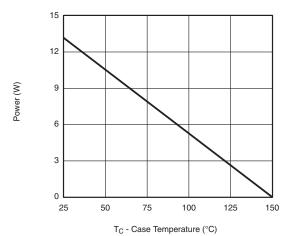


Safe Operating Area, Junction-to-Ambient

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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





Current Derating ^a

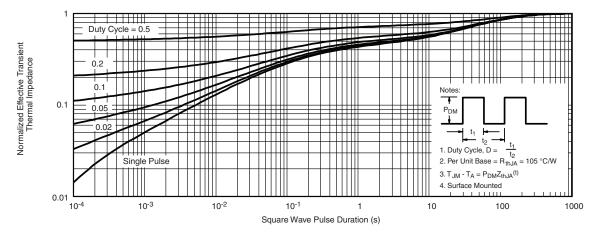
Power Derating

Note

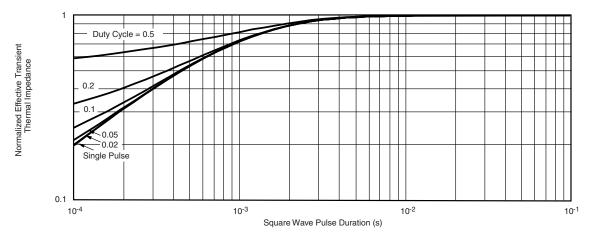
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



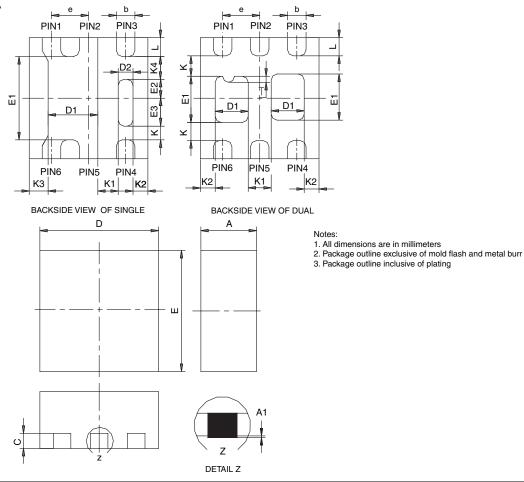
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65297.





PowerPAK® SC75-6L



	SINGLE PAD						DUAL PAD					
DIM	M	IILLIMETER	RS		INCHES		MILLIMETERS				INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						1
E	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						1
E3	0.32	0.37	0.42	0.013	0.015	0.017						1
е		0.50 BSC		0.020 BSC			0.50 BSC			0.020 BSC		
K		0.180 TYP			0.007 TYP)	0.245 TYP			0.010 TYP		
K1		0.275 TYP	0.275 TYP 0.011 TYP			0.320 TYP			0.013 TYP			
K2	0.200 TYP			0.200 BSC 0.008 TYP								
К3		0.255 TYP	255 TYP 0.010 TYP									
K4	0.300 TYP		0.012 TYP									
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
Т							0.03	0.08	0.13	0.001	0.003	0.005
ECN: C-	07/31 Re	v C 06-Au	g_07	1								

ECN: C-07431 - Rev. C, 06-Aug-07

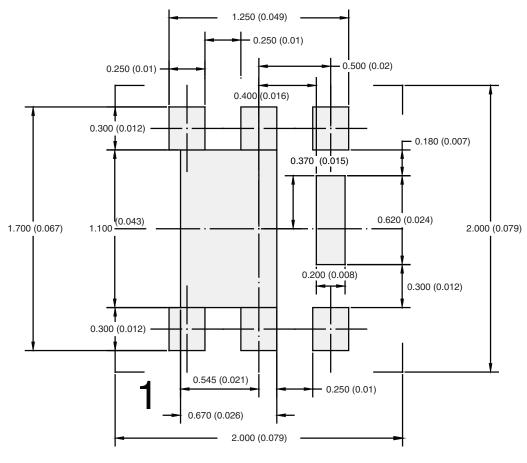
DWG: 5935

Document Number: 73000 06-Aug-07

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RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Single



Dimensions in mm/(Inches)

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ARRLICATION NOT



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